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line voltage

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Chen. et al.
Docket No.: Chen, et al. Unknown

October 20, 2003 EV 332 013 321 US

Atty: Phone:





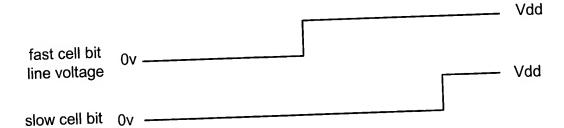
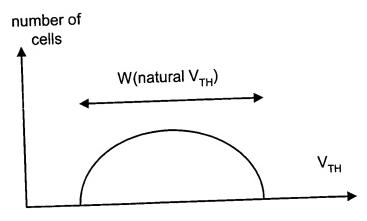


Fig. 2



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Fig. 3

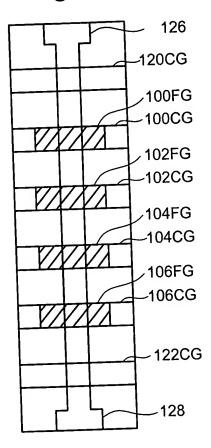


Fig. 4

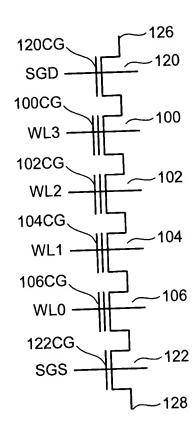
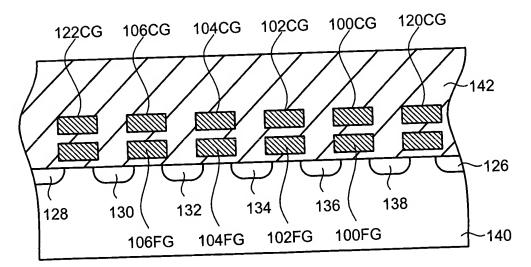


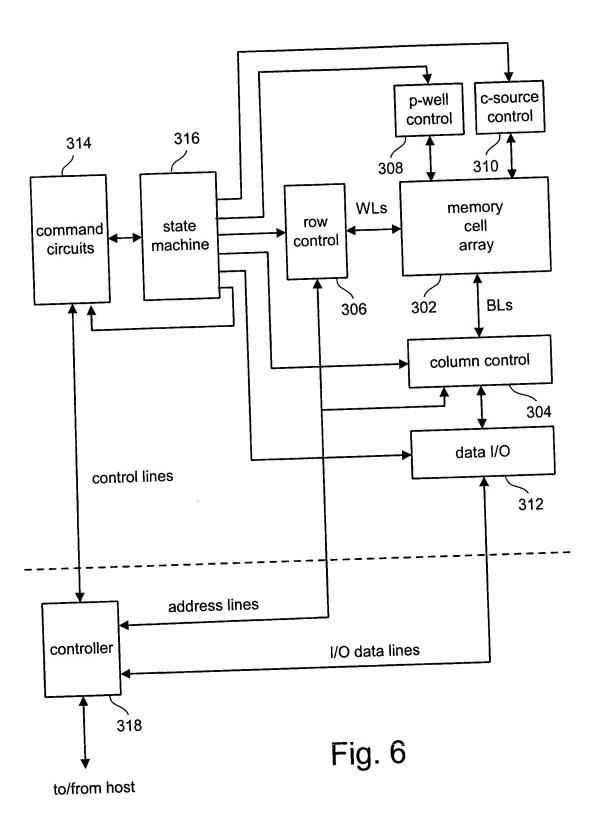
Fig. 5



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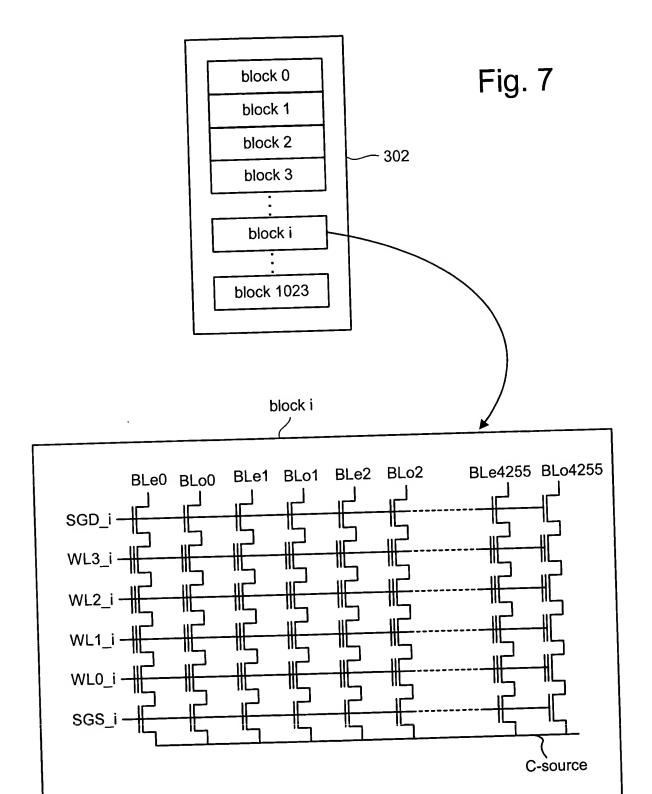
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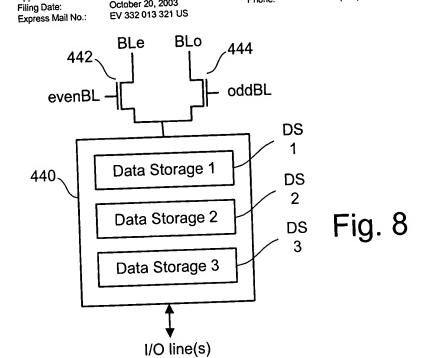
Title: Applicants: Appl. No.: Filing Date: Express Mail No.: Behavior Based Programming of Non-Volatile Memory
Chen, et al.
Docket No.:

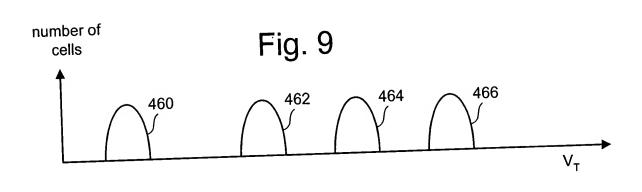
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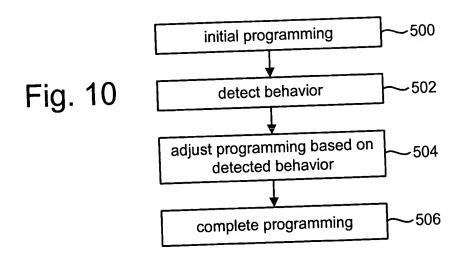


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Appl. No.: Unknown Atty: Burt Magen
Appl. No.: October 20, 2003 Phone: (415) 369-9660



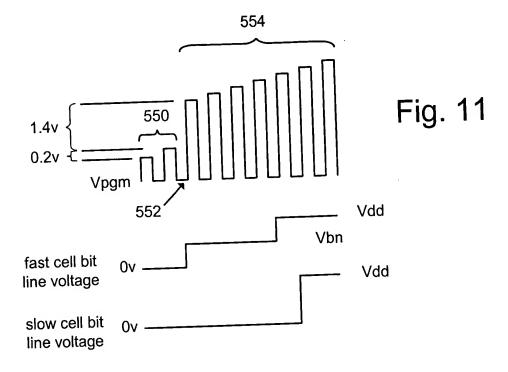


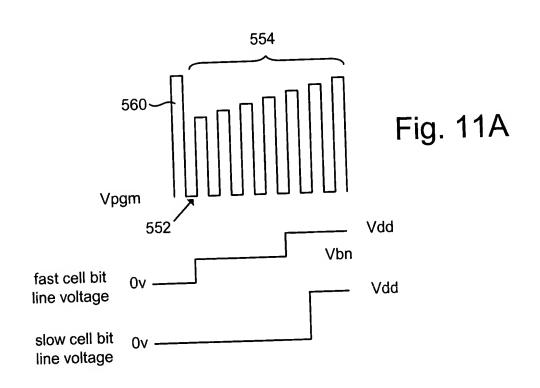


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Atty: Phone:

SAND-01012US0 Burt Magen (415) 369-9660

Filing Date: Express Mail No.: Unknown October 20, 2003 EV 332 013 321 US

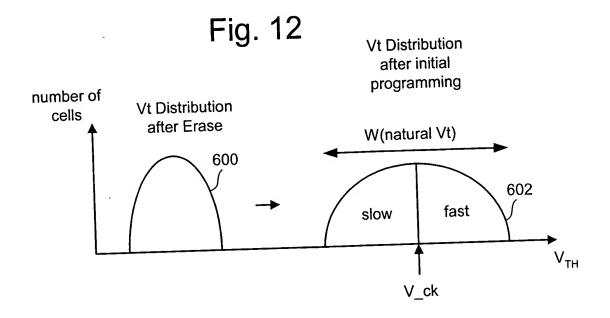


Fig. 13 630 read cell at V_ck 632 no yes cell turn on? 636 634 adjust bit line voltage to Vbn do not adjust bit line voltage

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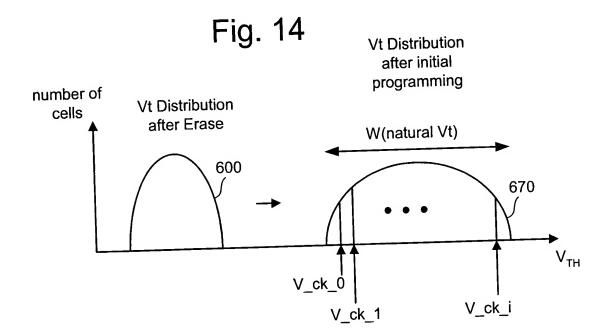
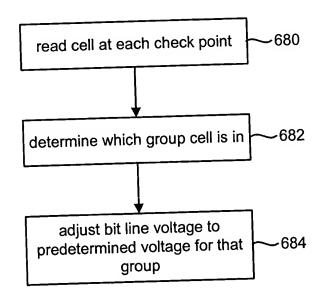


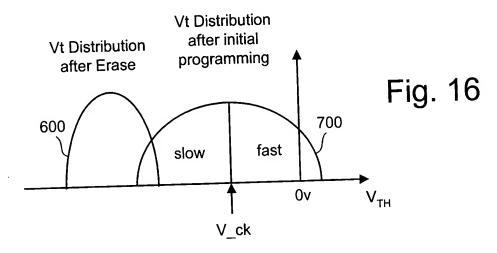
Fig. 15

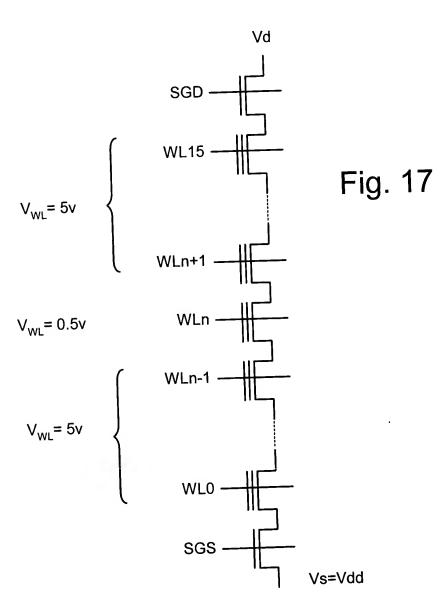


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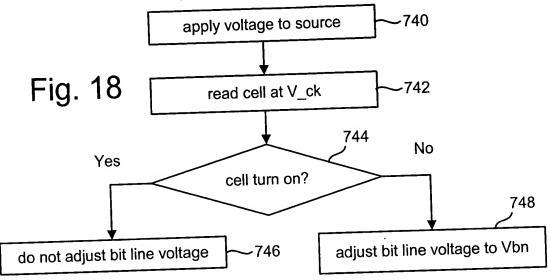
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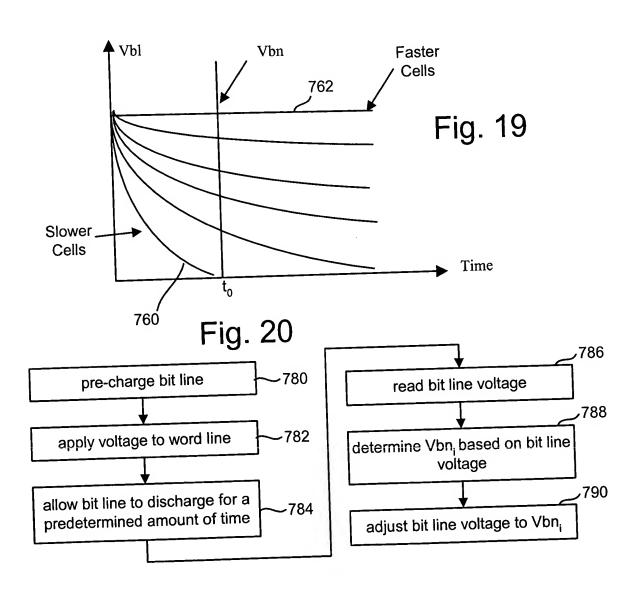
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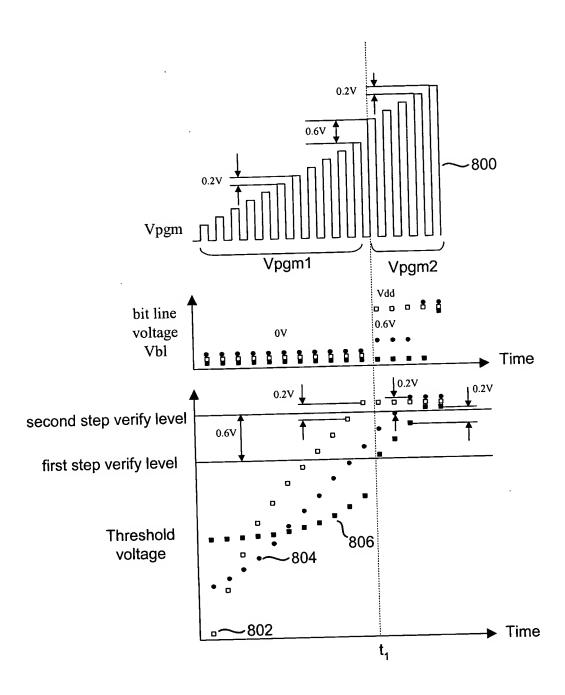
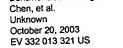


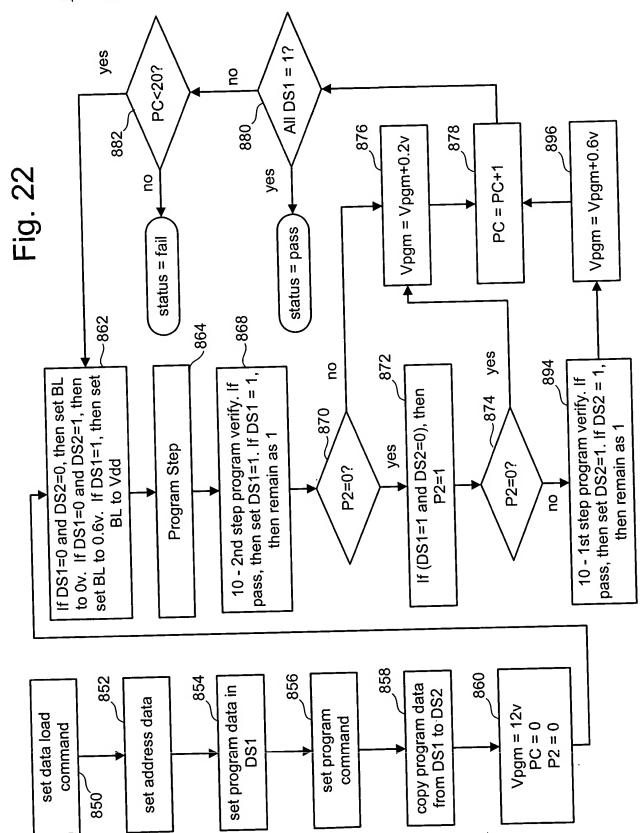
Fig. 21

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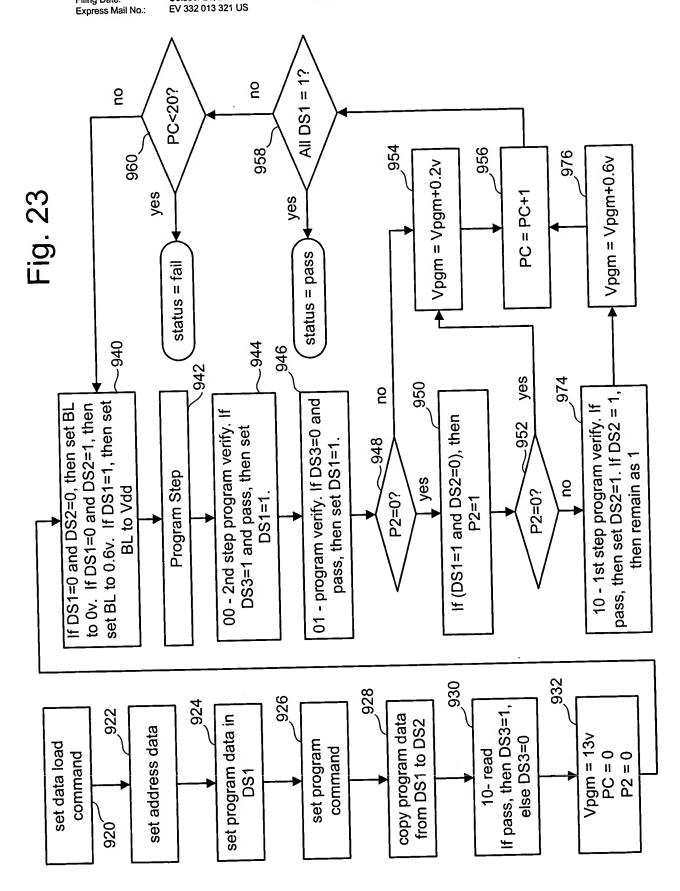


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Unknown Atty:
October 20, 2003 Phone:
EV 332 013 321 US

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| | 5 | program verify | Horl | | 8 | 15/ | 4.3 | 4.5V | | 2.6V | | 4.5V | | 4.50 | | 4.50 | | ≥ | | ∂ | | |
| | 00-2"-step | program verify | | 5 | 8 | ì | 4.5V | 4 5/ | 4.5V | | 3 | 4.5V | | 4.5V | | 4.5V | | ۸٥ | | 8 | | |
| | 00- 1step program verify | | - 2 | HorL | | | 4.50 | 4.5V | | 1.0V | | 4.5V | | 4.5V | | 4.5V | | λ0 | | Λ0 | | |
| | 10.2 nd .cfpn | no- z -step program verify | | HOLL | 2 | 5 | 4.5V | | VC.4 | 100 | 0.6V | | VC.+ | 4.5V | | 75.7 | 4.5V | | ∂ | | λο | |
| | 40 48 aton | program verify | | Horr | è | 3 | 4.5V | | 4.50 | | 0.0 | T. | 4.5V | 4.5V | | 15/ | 4.5V | | 8 | | 8 | |
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| | | Program Inhibit | | pp/ | | ₽ | 767 | 3 | \$0 | | Vicen | | 2 3 | | 10∕ | | 8 | | 8 | | 8 | |
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